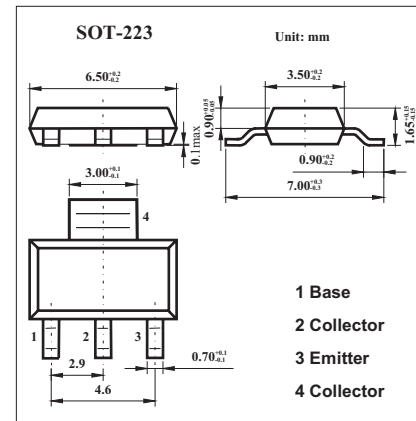


PNP Silicon High Voltage Transistor

FZT593

■ Features

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■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-2	A
Continuous Collector Current	I_C	-1	A
Base Current	I_B	-200	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

FZT593

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ.	Max	Unit
Breakdown Voltages	V _{(BR)CBO}	I _C =-100μA	-120			V
Breakdown Voltages	V _{(BR)CEO}	I _C =-10mA*	-100			V
Breakdown Voltages	V _{(BR)EBO}	I _E =-100μA	-5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =-100V			-100	nA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-4V			-100	nA
Collector-Emitter Cut-Off Current	I _{CES}	V _{CE} =-100V			-100	nA
Saturation Voltages	V _{CE(sat)}	I _C =-250mA, I _B =-25mA*			-0.2	V
		I _C =-500mA, I _B =-50mA*			-0.3	V
	V _{BE(sat)}	I _C =-500mA, I _B =-50mA*			-1.1	V
Base-Emitter Turn-on Voltage	V _{BE(on)}	I _C =-1mA, V _{CE} =-5V*			-1.0	V
Static Forward Current Transfer Ratio	h _{FE}	I _C =-1mA, V _{CE} =-5V	100			
		I _C =-250mA, V _{CE} =-5V*	100			
		I _C =-500mA, V _{CE} =-5V*	100	300		
		I _C =-1A, V _{CE} =-5V*	50			
Transition Frequency	f _T	I _C =-50mA, V _{CE} =-10V, f=100MHz	50			MHz
Output Capacitance	C _{obo}	V _{CB} =-10V, f=1MHz		5		pF

* Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%

■ Marking

Marking	FZT593
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